Yonghan Roh

List of Publications by Year
in descending order

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		567281	580821
65	734	15	25
papers	citations	h-index	g-index

66	66	66	1033
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Improving hole injection ability using a newly proposed WO3/NiOx bilayer in solution processed quantum dot light-emitting diodes. Current Applied Physics, 2022, 38, 81-90.	2.4	1
2	Improvement of Quantum Dot Light Emitting Device Characteristics by CdSe/ZnS Blended with HMDS (Hexamethyldisilazane). Applied Sciences (Switzerland), 2020, 10, 6081.	2.5	4
3	Improving Charge-Imbalanced Problem of Quantum Dot Light-Emitting Diodes with TPBi/ZnO Electron Transport Layer. Journal of Nanoscience and Nanotechnology, 2019, 19, 6152-6157.	0.9	1
4	Analysis of asymmetrical hysteresis phenomena observed in TMD-based field effect transistors. AIP Advances, 2018, 8, .	1.3	8
5	Analysis of Hysteresis Observed in Multi-Layered MoS₂ Field Effect Transistors. Journal of Nanoscience and Nanotechnology, 2017, 17, 7327-7330.	0.9	9
6	Off-state degradation with ac bias in PMOSFET. Microelectronics Reliability, 2016, 65, 16-19.	1.7	1
7	Roles of Residual Stress in Dynamic Refresh Failure of a Buried-Recessed-Channel-Array Transistor (B-CAT) in DRAM. IEEE Electron Device Letters, 2016, 37, 859-861.	3.9	7
8	Assembling CdSe/ZnS coreâ€“shell quantum dots on localized DNA nanostructures. RSC Advances, 2014, 4, 53201-53205.	3.6	1
9	FN-degradation of S-RCAT with different grain size and oxidation method. Microelectronic Engineering, 2014, 119, 32-36.	2.4	3
10	Negative effect of Au nanoparticles on an IGZO TFT-based nonvolatile memory device. Journal of the Korean Physical Society, 2014, 64, 337-340.	0.7	2
11	n- and p-Type Doping Phenomenon by Artificial DNA and M-DNA on Two-Dimensional Transition Metal Dichalcogenides. ACS Nano, 2014, 8, 11603-11613.	14.6	85
12	Poly-4-vinylphenol and poly(melamine-co-formaldehyde)-based graphene passivation method for flexible, wearable and transparent electronics. Nanoscale, 2014, 6, 3830.	5.6	21
13	Effect of body bias on negative bias temperature instability in pMOSFET with SiON gate dielectrics. Solid-State Electronics, 2014, 91, 127-129.	1.4	0
14	Characteristics of fabricated catalytic combustible micro gas sensor with low power consumption for detecting methane leakage of compressed natural gas bus. Journal of Electroceramics, 2013, 31, 280-285.	2.0	4
15	Depth-controllable ultra shallow Indium Gallium Zinc Oxide/Gallium Arsenide hetero junction diode. Journal of Alloys and Compounds, 2013, 561, 228-230.	5.5	4
16	Analysis of dynamic retention characteristics of NWL scheme in high density DRAM. , 2013, , .		0
17	Characteristics of Ultrashallow Hetero Indiumâ€“Galliumâ€“Zincâ€“Oxide/Germanium Junction. IEEE Electron Device Letters, 2012, 33, 1363-1365.	3.9	2
18	Effect of post-fabrication thermal annealing on Fermi-level pinning phenomenon in metal-pentacene junctions. Organic Electronics, 2012, 13, 1511-1515.	2.6	6

#	Article	IF	Citations
19	Sizeâ€Controllable DNA Rings with Copperâ€Ion Modification. Small, 2012, 8, 374-377.	10.0	22
20	Structural and functional stabilities of artificially designed DNA ultra-thin films grown by silica Assistance. Current Applied Physics, 2012, 12, 1207-1211.	2.4	5
21	Leakage current reduction in pentacene-based thin film transistor using asymmetric source/drain electrodes. Organic Electronics, 2012, 13, 1056-1059.	2.6	6
22	Coverage Control of DNA Crystals Grown by Silica Assistance. Angewandte Chemie - International Edition, 2011, 50, 9145-9149.	13.8	36
23	Electrical characteristics of oxygen doped DNA molecules. Thin Solid Films, 2011, 519, 7057-7059.	1.8	4
24	Uniform formation of Au coated polystyrene coreâ€“shell structure using metallization process. Thin Solid Films, 2011, 519, 7120-7123.	1.8	1
25	Electrical Characteristics and Doping Mechanism of DNA Molecules Doped with Iodine Solutions. Journal of Nanoscience and Nanotechnology, 2010, 10, 3484-3488.	0.9	1
26	Fabrication of Highly Uniform Conductive Polypyrrole Nanowires with DNA Template. Journal of Nanoscience and Nanotechnology, 2010, 10, 3180-3184.	0.9	9
27	Selective Alignment of Gold Nanowires Synthesized With DNA as Template by Surface-Patterning Technique. IEEE Nanotechnology Magazine, 2010, 9, 254-257.	2.0	11
28	Selective Formation of a Latticed Nanostructure with the Precise Alignment of DNA-Templated Gold Nanowires. Langmuir, 2010, 26, 18315-18319.	3.5	18
29	Selective Growth of the Silicon-Oxide Nanodot Array Using Nanosphere Lithography and Liquid-Phase Deposition. IEEE Nanotechnology Magazine, 2010, 9, 361-366.	2.0	5
30	Selective liquid phase deposition of silicon oxide at low temperature for nanometer-scale structures. Thin Solid Films, 2009, 517, 3947-3949.	1.8	1
31	Fabrication and characterization of DNA-templated conductive gold nanoparticle chains. Journal of Applied Physics, 2009, 105, 074302.	2.5	15
32	Characteristics of Hf-silicate Interfacial Layers Formed by WetEtching. Journal of the Korean Physical Society, 2009, 55, 1022-1025.	0.7	4
33	Formation of Au Nanowires using DNA Molecules as Template. Journal of the Korean Physical Society, 2009, 55, 1892-1895.	0.7	0
34	Fabrication of SiO2 nano-dots by block copolymer lithography and liquid phase deposition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 147, 209-212.	3.5	11
35	Characteristics of gold nanowires and UV spectral changes by interaction between gold nanoparticles and DNA. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 2545-2550.	2.7	2
36	Performance and characteristics of imprint mould fabricated by liquid-phase deposition. Superlattices and Microstructures, 2008, 44, 520-527.	3.1	3

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37	Formation of nanometer-scale structures using conventional optical lithography. Thin Solid Films, 2008, 516, 1489-1492.	1.8	14
38	Partial Crystallization of $hbox{HfO}_{2}$ for Two-Bit/Four-Level SONOS-Type Flash Memory. IEEE Transactions on Electron Devices, 2007, 54, 3177-3185.	3.0	15
39	Silicon Dioxide Deposited by Using Liquid Phase Deposition at Room Temperature for Nanometer-Scaled Isolation Technology. Journal of the Korean Physical Society, 2007, 51, 1191.	0.7	5
40	Electrical Characterizations of HfO2/Al2O3/Si as Alternative Gate Dielectrics. Journal of the Korean Physical Society, 2007, 51, 238.	0.7	13
41	Formation of Î»-DNA's in Parallel- and Crossed-Line Arrays by Molecular Combing and Scanning-Probe Lithography. Nano Letters, 2006, 6, 1334-1338.	9.1	27
42	Formation of nanometer-scale gap electrodes based on a plasma ashing technique. Thin Solid Films, 2006, 515, 744-747.	1.8	11
43	Improved performance of multi-giga bit NAND flash using <100> channel orientation. , 2006, , .		0
44	Controlled gold nanoparticle assembly on DNA molecule as template for nanowire formation. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 1327-1331.	2.1	17
45	Asymmetrical Increase of Memory Window in MFIS Devices After Avalanche Hole Injection. Ferroelectrics, 2005, 329, 113-118.	0.6	0
46	Effect of calcination on the crystallinity of sputtered TiO2 thin films as studied by Raman scattering. Crystal Research and Technology, 2005, 40, 222-225.	1.3	7
47	Roles of buffer solution and substrate surface on the characteristic of DNA network formed on SiO2. Materials Science and Engineering C, 2003, 23, 851-855.	7.3	7
48	Post-etch residue removal in BCB/Cu interconnection structure. Thin Solid Films, 2003, 435, 238-241.	1.8	5
49	Formation of Reliable HfO2/HfSixOyGate-Dielectric for Metal-Oxide-Semiconductor Devices. Japanese Journal of Applied Physics, 2002, 41, 6904-6907.	1.5	25
50	Argon and nitrogen implantation effects on the structural and optical properties of vacuum evaporated cadmium sulphide thin films. Semiconductor Science and Technology, 2002, 17, 97-103.	2.0	54
51	Impact of floating gate dry etching on erase characteristics in NOR flash memory. IEEE Electron Device Letters, 2002, 23, 476-478.	3.9	89
52	The effect of deposition temperature on the electrical and physical properties of the Ba(Zr,Ti)O3 thin films. Journal of Non-Crystalline Solids, 2002, 303, 190-193.	3.1	20
53	Electrical properties of the MOS structures using strained (Ba0.5, Sr0.5)TiO3thin films. Ferroelectrics, 2001, 259, 269-275.	0.6	0
54	The improvement of the SiO2/InAs interface properties with the aid of fast electron irradiation in a direct current sputter deposition system. Applied Surface Science, 2001, 172, 295-300.	6.1	2

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55	Electrical Characteristics of Al/CeO2(200)/Si(100) and Al/CeO2(111)/Si(100) Metal-Insulator-Semiconductor Structure. Japanese Journal of Applied Physics, 2001, 40, L564-L566.	1.5	4
56	Properties of HfO2/Hf-Silicate/Si Structures with Hf-Silicate Formed by Hf Metal Deposition and Subsequent Reaction. Japanese Journal of Applied Physics, 2001, 40, L813-L816.	1.5	6
57	Hysteresis caused by defects in buffer layer of metal-ferroelectric-insulator-semiconductor (MFIS) devices. Integrated Ferroelectrics, 2001, 40, 245-254.	0.7	3
58	Effects of deposition parameters on the crystallinity of CeO2 thin films deposited on Si(100) substrates by r.f.-magnetron sputtering. Thin Solid Films, 2000, 360, 154-158.	1.8	52
59	Analysis of Current Components Observed by Cyclic Current-Voltage Measurement in Metal-Oxide-Semiconductor Capacitors. Japanese Journal of Applied Physics, 2000, 39, L1152-L1154.	1.5	0
60	Significant reduction of leakage current in the TiO2/Si structure by the insertion of the CeO2 intermediate layer. Applied Physics Letters, 2000, 77, 729-731.	3.3	15
61	Electrical characterizations of MgTiO3 thin films grown on Si. Integrated Ferroelectrics, 2000, 31, 359-366.	0.7	1
62	The Hysteresis Caused by Interface Trap and Anomalous Positive Charge in Al/CeO2-SiO2/Silicon Capacitors. Japanese Journal of Applied Physics, 1997, 36, L1681-L1684.	1.5	22
63	Electrical characteristics of CeO/sub 2/ buffer layer for a FRAM. , 0, , .		0
64	Influence of plasma edge damage on erase characteristics of NOR flash EEPROM using channel erase method. , 0, , .		2
65	Triple boron doped silicon for selective epitaxial growth of 3D NAND flash memory. Journal of the Korean Physical Society, 0, , 1.	0.7	0